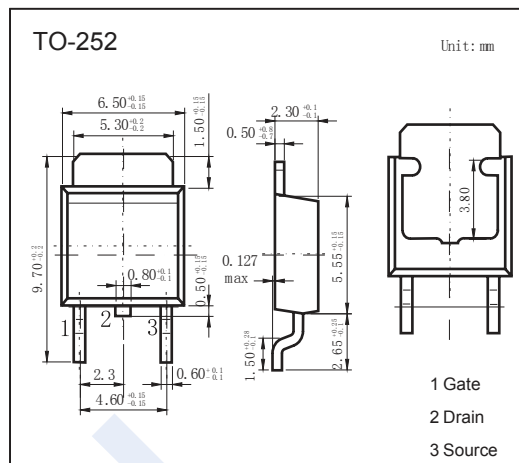
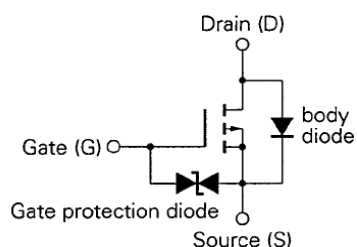


P-Channel MOSFET

2SJ324-Z

■ Features

- $V_{DS} (V) \approx -30V$
- $I_D \approx -2 A$
- $R_{DS(ON)} < 250m\Omega$ ($V_{GS} \approx -10V$)
- $R_{DS(ON)} < 520m\Omega$ ($V_{GS} \approx -4V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-2	A
Pulsed Drain Current (Note.1)	I_{DM}	-8	
Power Dissipation $T_c = 25^\circ C$ $T_a = 25^\circ C$	P_D	20	W
		1	
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $PW \leq 10\mu s$, Duty Cycle $\leq 1\%$

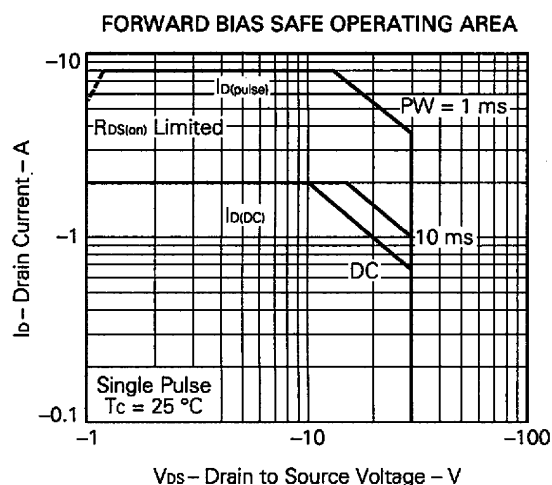
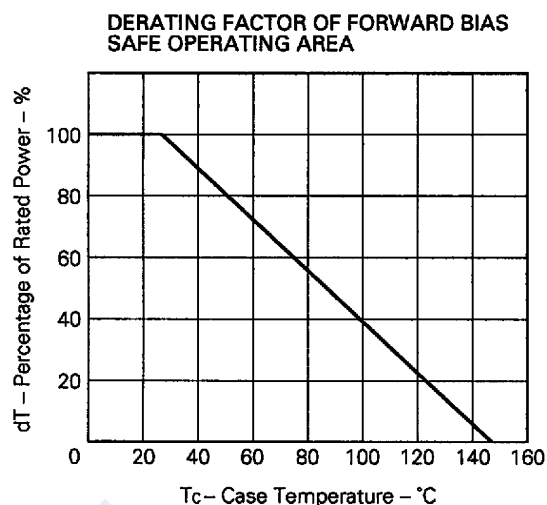
P-Channel MOSFET

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■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D = -250\ \mu\text{A}$, $V_{GS} = 0\text{V}$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{V}$, $V_{GS} = 0\text{V}$			-10	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 16\text{V}$			± 10	μA
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$	-1		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{V}$, $I_D = -1\text{A}$			250	m Ω
		$V_{GS} = -4\text{V}$, $I_D = -0.8\text{A}$			520	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{V}$, $I_D = -1\text{A}$	1	1.9		S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		330		pF
Output Capacitance	C_{oss}			290		
Reverse Transfer Capacitance	C_{rss}			105		
Total Gate Charge	Q_g	$V_{GS} = -10\text{V}$, $V_{DS} = -24\text{V}$, $I_D = -2\text{A}$		12		nC
Gate Source Charge	Q_{gs}			1.5		
Gate Drain Charge	Q_{gd}			4.5		
Turn-On DelayTime	$t_{d(on)}$	$V_{GS(on)} = -10\text{V}$, $V_{DS} = -15\text{V}$, $I_D = -1\text{A}$, $R_L = 15\ \Omega$, $R_{GEN} = 10\ \Omega$		7		ns
Turn-On Rise Time	t_r			35		
Turn-Off DelayTime	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			30		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2\text{A}$, $V_{GS} = 0$, $dI/dt = 50\text{A}/\mu\text{s}$		50		nC
Body Diode Reverse Recovery Charge	Q_{rr}			40		
ESD Voltage	V_{ESD}	$C = 200\text{pF}$, $R = 0$, Single Pulse		± 130		V
Diode Forward Voltage	V_{SD}	$I_F = -2\text{A}$, $V_{GS} = 0\text{V}$		-0.9		V

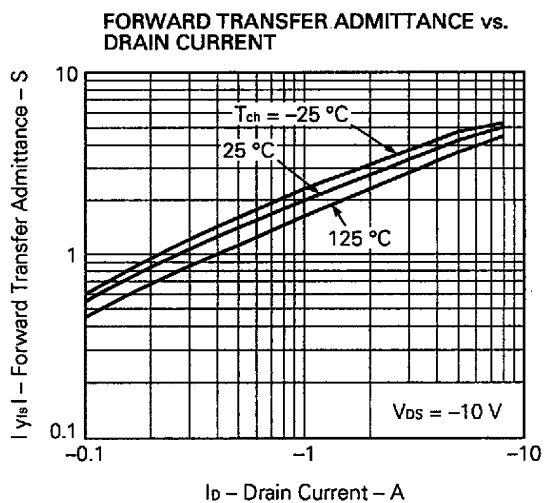
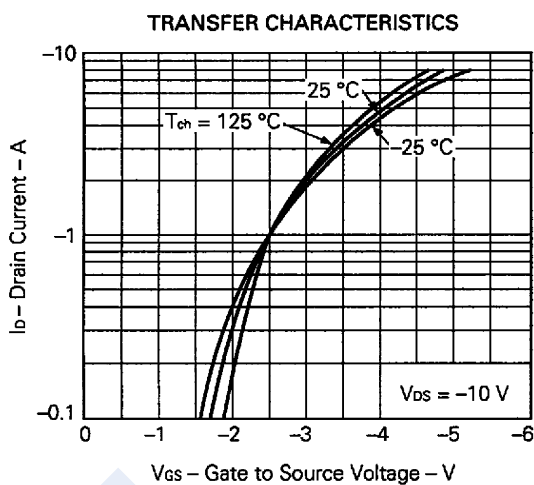
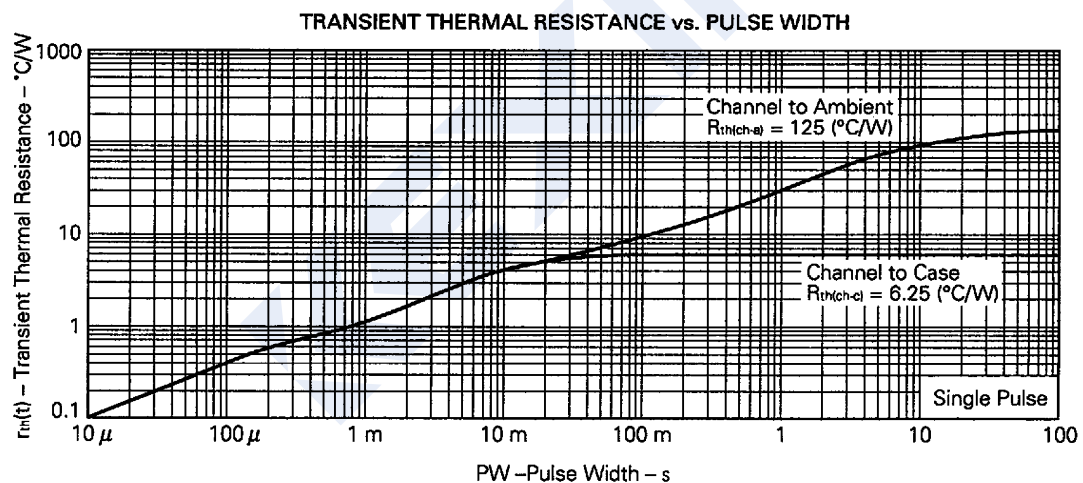
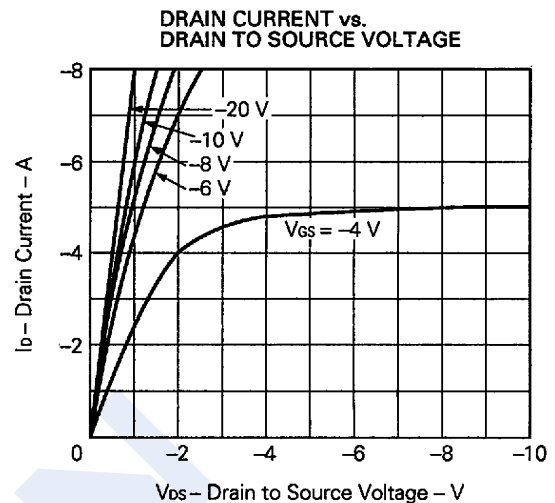
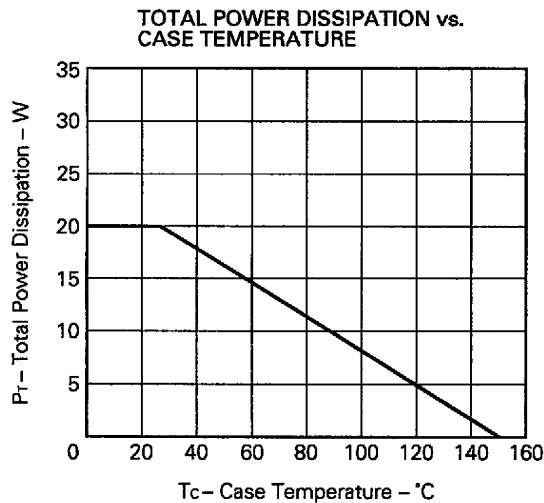
■ Typical Characteristics



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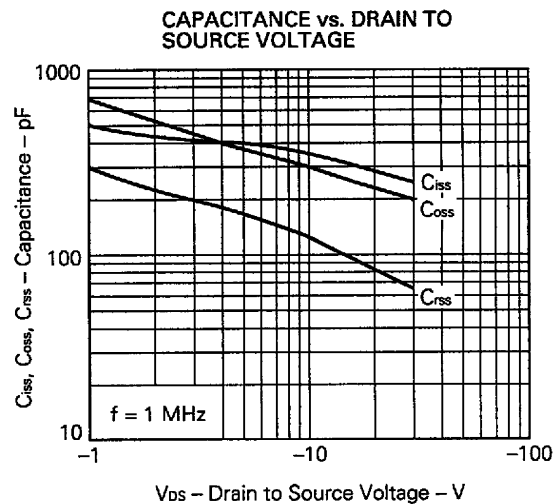
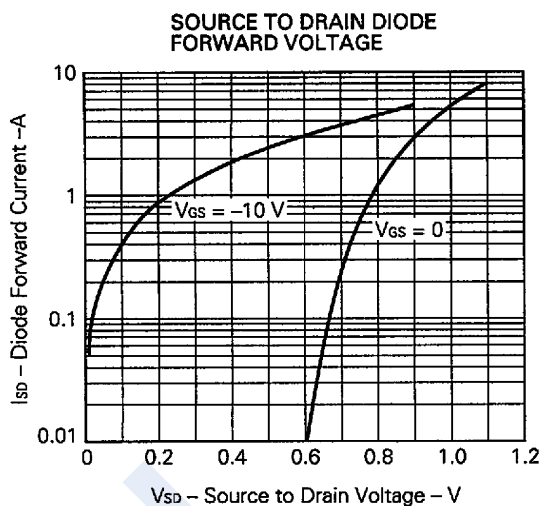
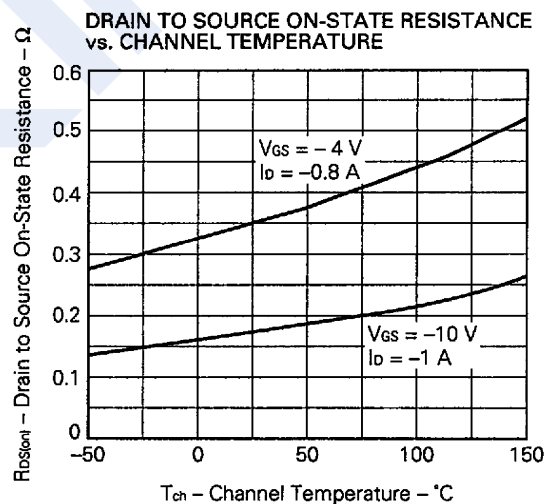
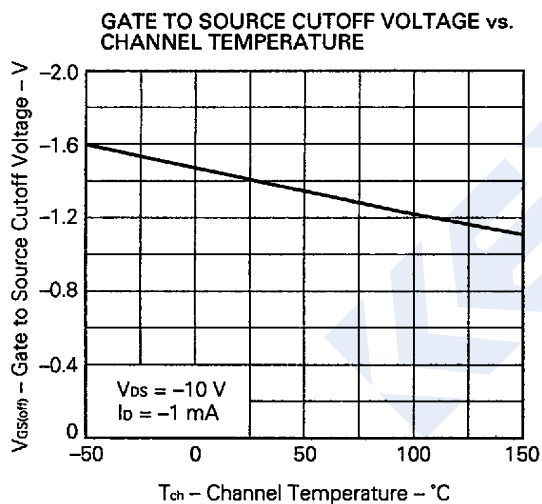
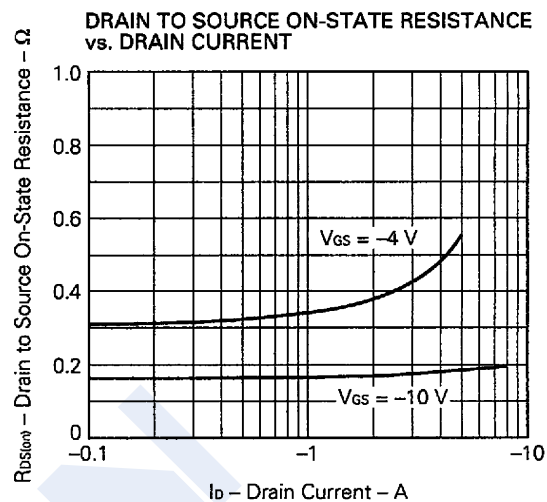
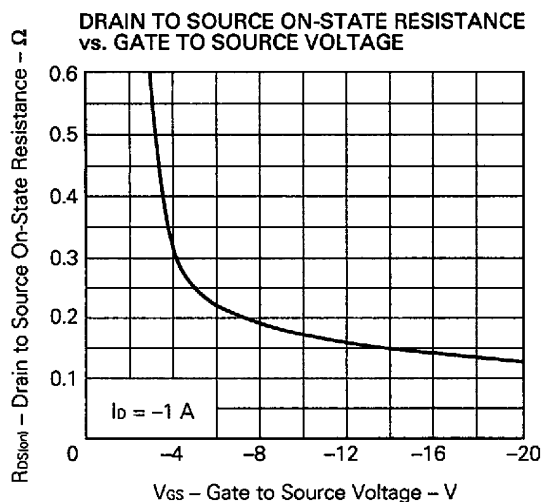
Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics

